

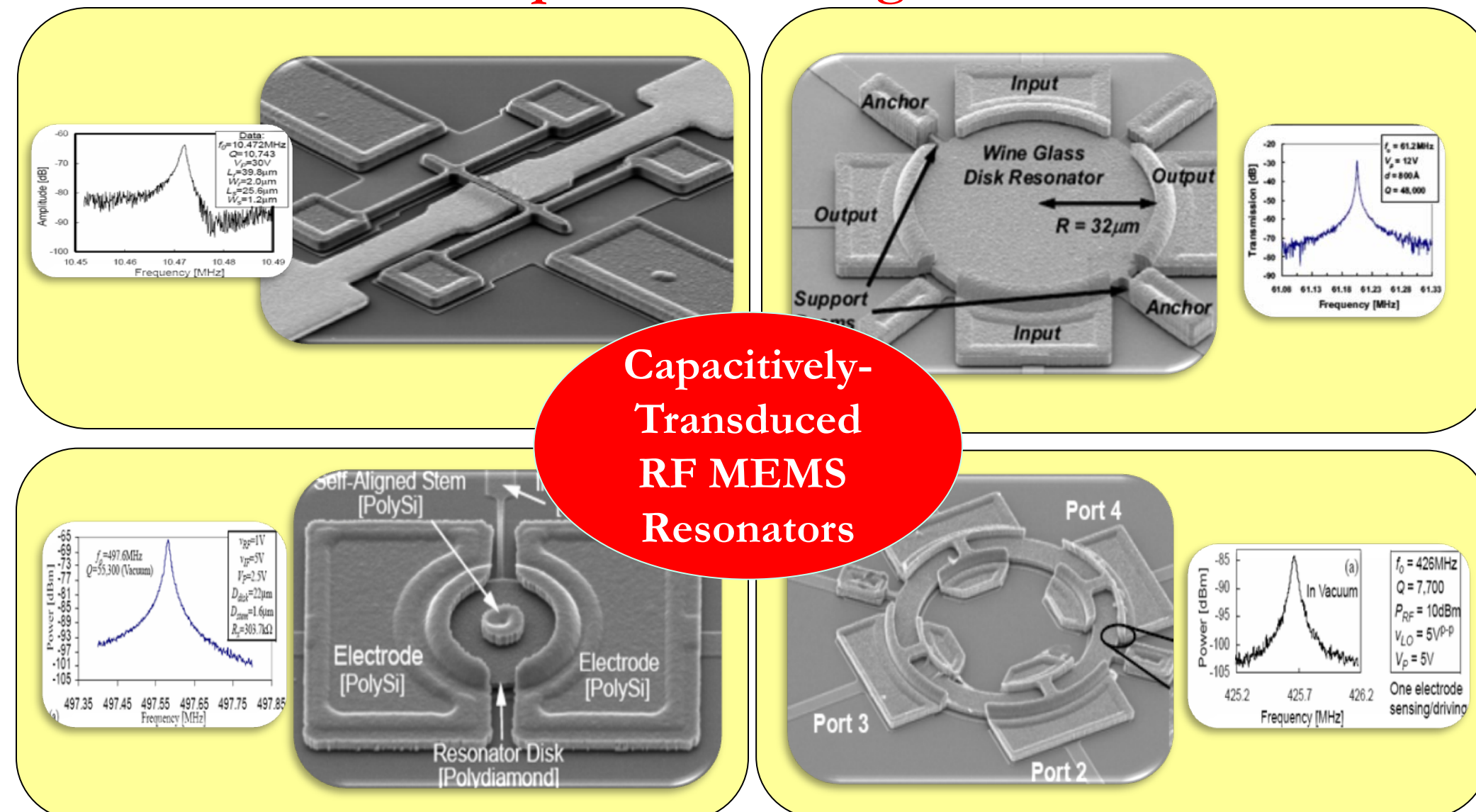
Atomic Layer Deposition (ALD) Enabled RF MEMS Resonator by IC-Compatible Process

Mian Wei, Jing Wang
Department of Electrical Engineering
University of South Florida

Introduction

Capacitively-transduced MEMS resonators

- ✓ Higher Q-factor ($Q > 160,000$)
- ✓ High frequency ($f > 6\text{GHz}$)
- ✓ Radius controlled frequency
- ✓ Low temperature coefficient
- ✗ High impedance
- ✗ Low power handling



Motivation

In spite to high-Q, concerns about **impedance matching** and **power handling** of the micromechanical resonator reveal due to its orders of magnitude smaller dimensions comparing to its bulky counterparts, such as quartz crystals.

Impedance Matching

- ✓ Reduced resonator-to-electrodes gap
- ✓ High dielectric material
- ✓ Increased overlap area

Power handling

- ✓ Large arrays of identical devices

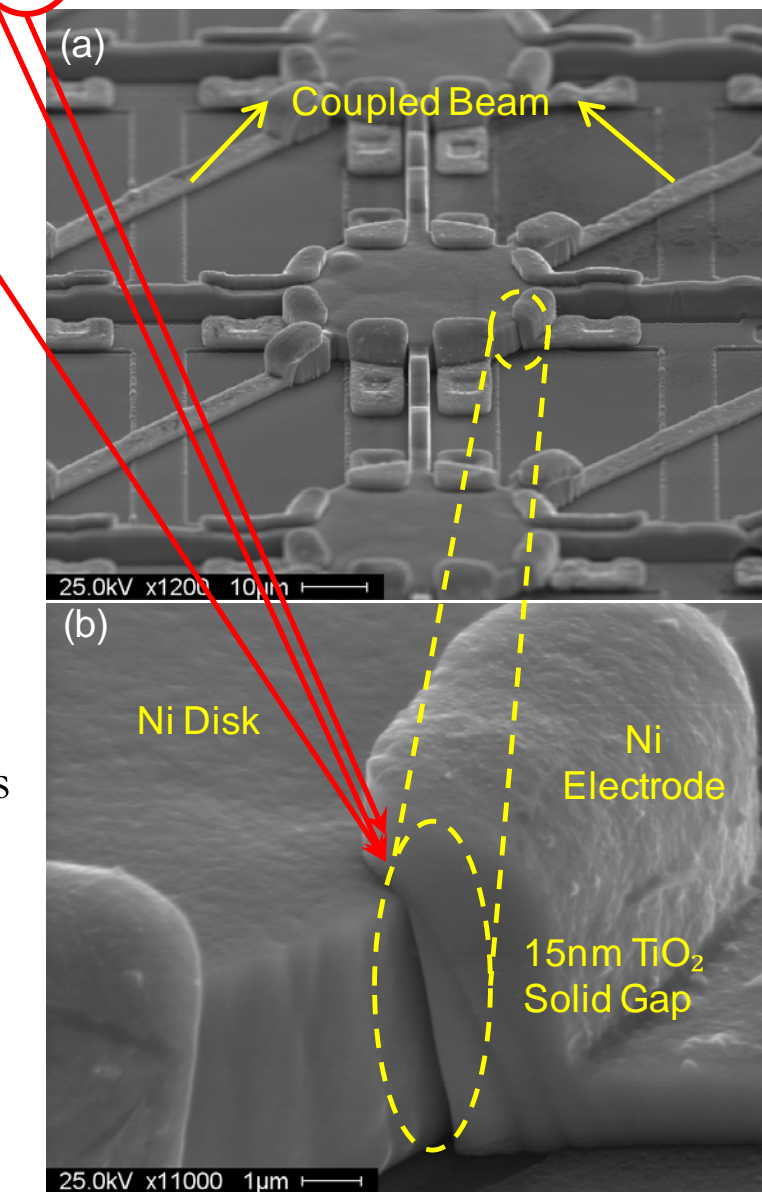
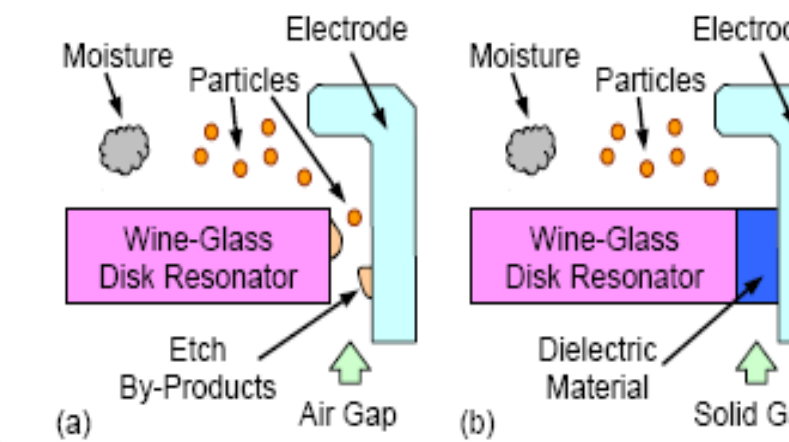
Impedance Matching Design

ALD Solid Gap vs. Air Gap

- Ease of the process
- Eliminate the particles
- Reduce characteristic impedance

$$R_{x(\text{Air Gap})} = \frac{v_i}{i_o} \cong \frac{k_r}{\omega_o V_p^2} \cdot \frac{d_o^4}{\epsilon_r^2 \epsilon_o^2 A_o^2} \cdot Q_{(\text{Air Gap})}$$

d_o : disk-to-electrode gap
 ϵ_r : dielectric constant of the gap material
 A_o : overlap area



Advantages of ALD

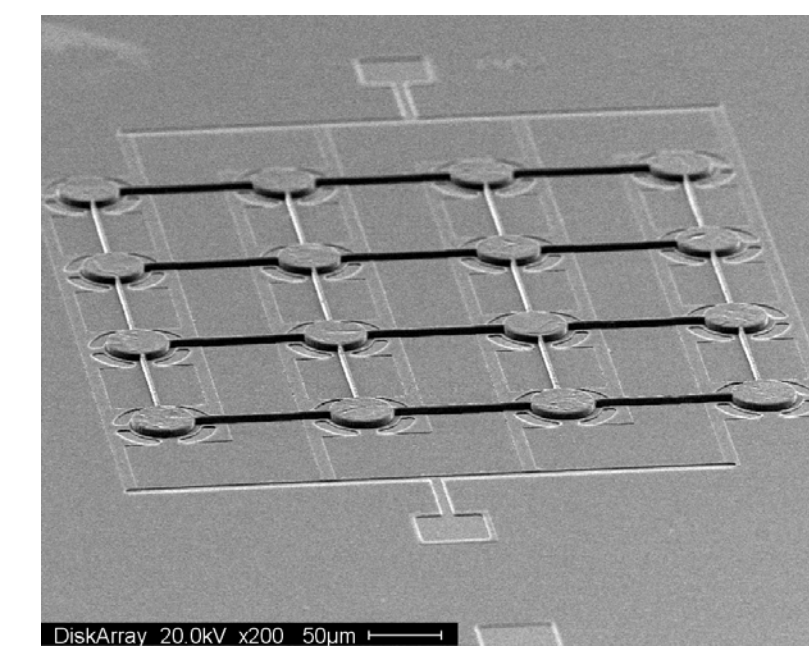
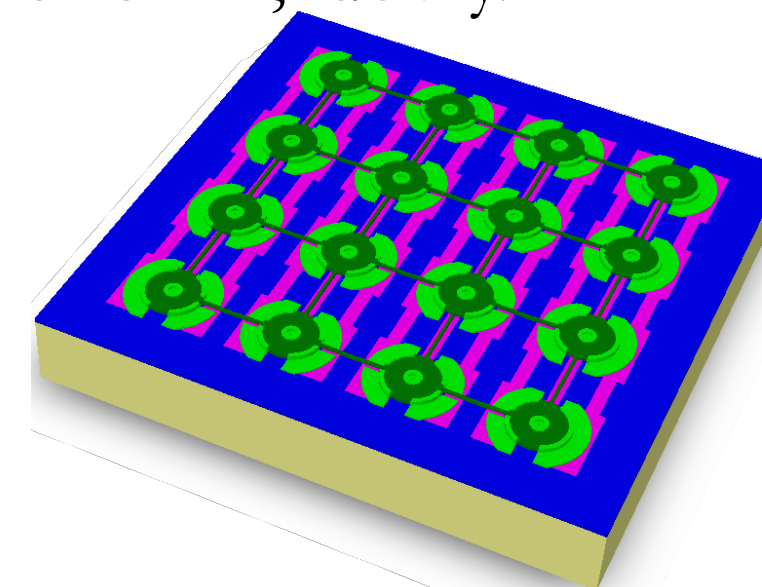
- Ultra Thin (~nm)
- High- ϵ Dielectric Material
- Atomically Controlled Thickness
- Low Temperature (~100 °C)
- Conformal and Uniform

Savannah 100 ALD
Cambridge Nanotech Inc.

High Power Handling Design

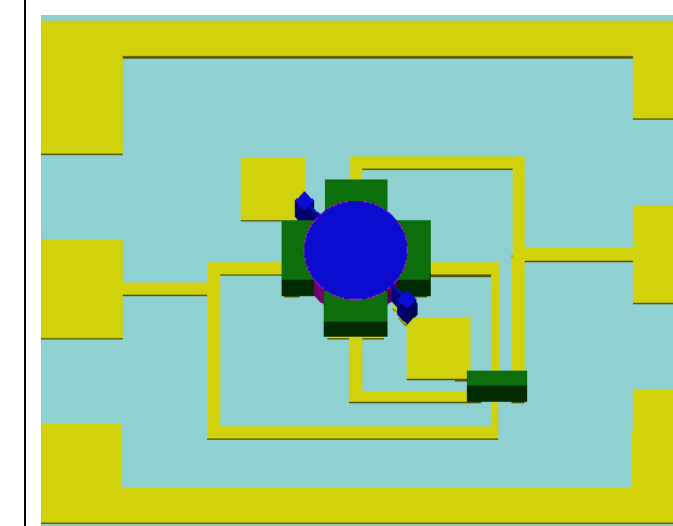
$$P_{0\text{max},n} = n \cdot \frac{\omega_o}{Q_n} k_r a^2 d_o^2 \quad (n: \text{number of resonators})$$

A $n \times n$ array has capability of increase the power handling by a factor of n^2 , ideally.

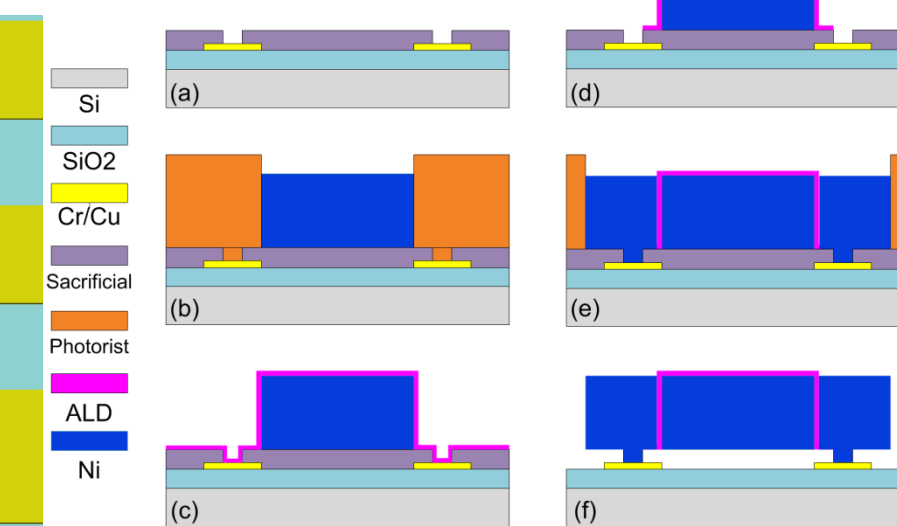


Fabrication

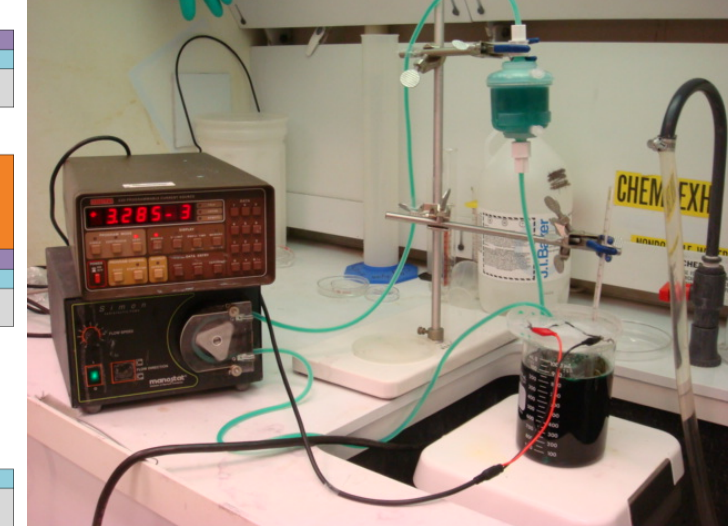
3D Schematic View



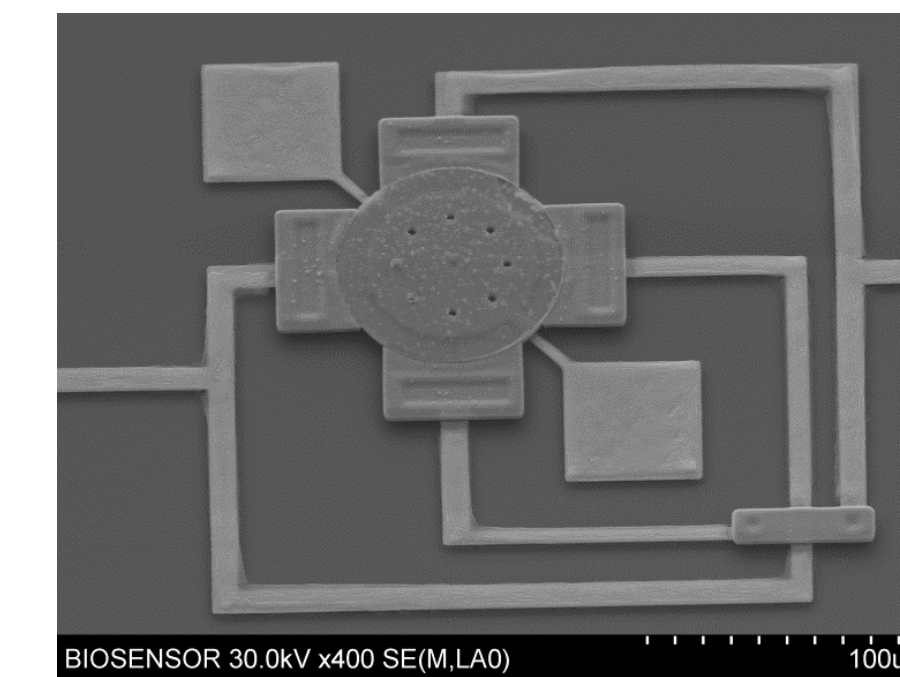
Process Flow



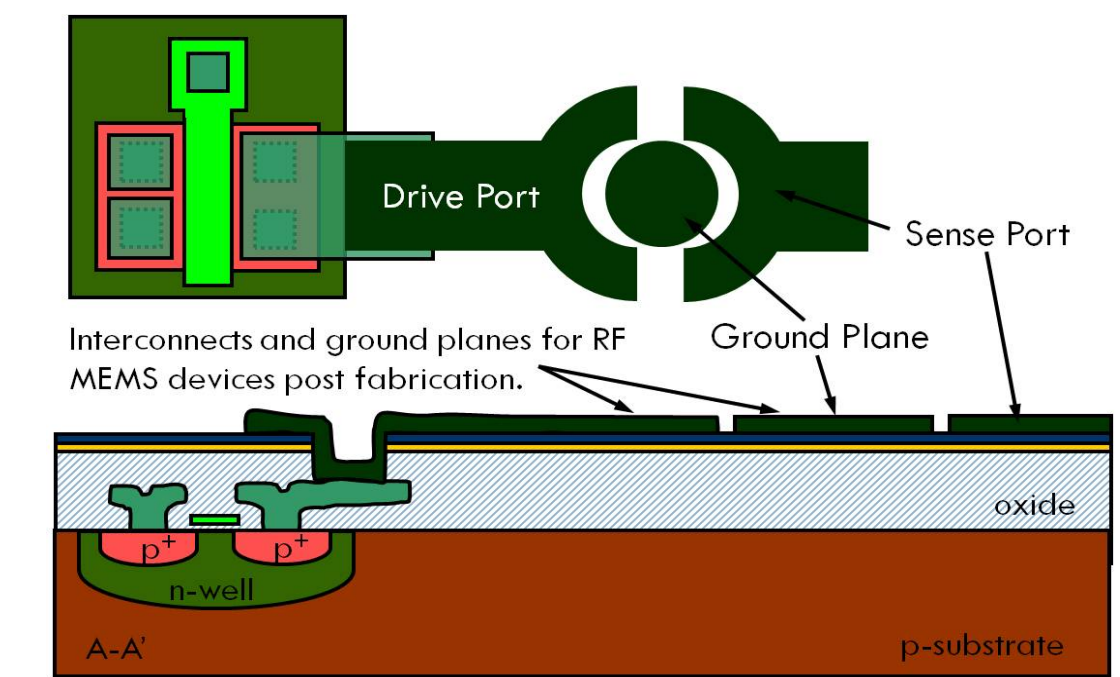
Ni Electroplating Set-up



SEM Photo of a Fabricated Device



Post-CMOS of Integration



Applications

